

In the Claims:

Please enter the following amended claims 24, 31, and 37:

*True*  
*DI*  
*✓*

24. (Twice Amended) A structure in a semiconductor chip, said structure comprising:

- a first area of a dielectric, said first area of said dielectric having a first permeability;
- a second area of said dielectric, said second area of said dielectric having a second permeability, said second permeability being higher than said first permeability;
- a permeability conversion material interspersed within said second area of said dielectric, said permeability conversion material having a third permeability, said third permeability being greater than said first and said second permeabilities;
- a conductor patterned in said second area of said dielectric, said permeability conversion material not being situated underneath said conductor.

*DI*  
*CA*

31. (Once Amended) A structure in a semiconductor chip, said structure comprising:

- a dielectric having a first permeability;
- a permeability conversion material having a second permeability, said permeability conversion material being interspersed within said dielectric, wherein said second permeability is greater than said first permeability;

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an inductor comprising a conductor patterned within said dielectric, said  
conductor having first and second terminals, said first and second terminals of  
said conductor being respectively first and second terminals of said inductor, said  
permeability conversion material not being situated underneath said inductor.

37. (Once Amended) A semiconductor chip comprising:

a first dielectric area having a first permeability;

a second dielectric area having a permeability conversion material interspersed therein  
such that a permeability of said second dielectric area is higher than said first permeability;

an inductor patterned in said second dielectric area, said inductor having first and  
second connection terminals, said first and second connection terminals being capable of  
providing connection to a device fabricated in said first dielectric area of said  
semiconductor chip, said permeability conversion material not being situated underneath  
said inductor.